



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#20/C
7/26/01
Rst

In re the Application of:

Docket No.: TIJ-24816

Hiroyuki Enomoto, et al.

Serial No.: 09/019,087

Art Unit: 1765

Filed: February 5, 1998

Examiner: V. Perez Ramos

Title: Manufacturing Method of Semiconductor IC Device

AMENDMENT UNDER 37 CFR 1.116

Assistant Commissioner for Patents
Washington, D. C. 20231

MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(A) I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Box AF, Assistant Commissioner for Patents, Washington, D.C. 20231.

[Signature] 7/11/01
William B. Kempler, Reg. No. 28,228 Date

Sir:

In response to the Office Action dated February 12, 2001 in the above-identified patent application, please make the following amendments.

IN THE CLAIMS:

RECEIVED
JUL 19 2001
IC 1700 MAIL ROOM

Sub D.1
C1

1. (Three Times Amended) A manufacturing method of a semiconductor IC device, comprising the following steps:
- forming an insulating film on a semiconductor substrate or SOI substrate;
 - forming a first mask film on the insulating film;
 - forming a resist film on the first mask film, the resist film being used as an etching mask to form an opening on the first mask film, followed by the formation of trenches on the insulating film exposed from the opening said trenches being made deeper than a thickness of said insulating film so as to penetrate into a portion of said substrate;
 - forming, after the resist film is removed, a second mask film on the semiconductor substrate or SOI substrate, said second mask film covering side walls and a bottom of the trenches;